



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ (Ω)	I_D (A)
60	0.050 @ $V_{GS}=10V$	7.0
	0.070 @ $V_{GS}=4.5V$	



Description

This new generation Trench MOSFET from Zetex features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Features

- Low on-resistance
- Fast switching speed
- Low gate drive
- SO8 package

Applications

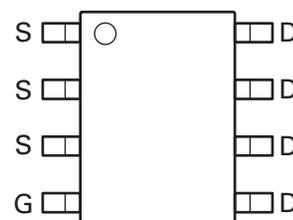
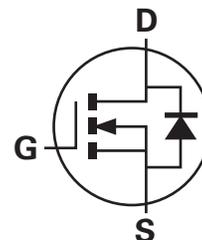
- DC-DC Converters
- Power management functions
- Disconnect switches
- Motor control

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
NK-ZXMN6A25N8TA	7	12	500

Device marking

NK-ZXMN6A25



Top view

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-Source voltage	V_{DS}	60	V
Gate-Source voltage	V_{GS}	± 20	V
Continuous Drain current @ $V_{GS}=10V$; $T_A=25^\circ C$ (b) @ $V_{GS}=10V$; $T_A=70^\circ C$ (b) @ $V_{GS}=10V$; $T_A=25^\circ C$ (a) @ $V_{GS}=10V$; $T_L=25^\circ C$ (a)(d)	I_D	5.7 4.5 4.3 7.0	A
Pulsed Drain current (c)	I_{DM}	25.7	A
Continuous Source current (Body diode) (b)	I_S	4.1	A
Pulsed Source current (Body diode) (c)	I_{SM}	25.7	A
Power dissipation at $T_A=25^\circ C$ (a) Linear derating factor	P_D	1.56 12.5	W mW/ $^\circ C$
Power dissipation at $T_A=25^\circ C$ (b) Linear derating factor	P_D	2.8 22.2	W mW/ $^\circ C$
Power dissipation at $T_L=25^\circ C$ (d) Linear derating factor	P_D	4.14 33.1	W mW/ $^\circ C$
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	$^\circ C$

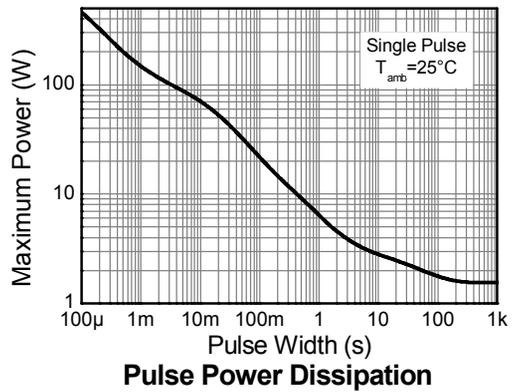
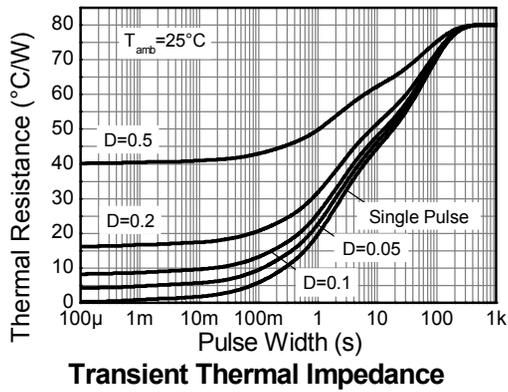
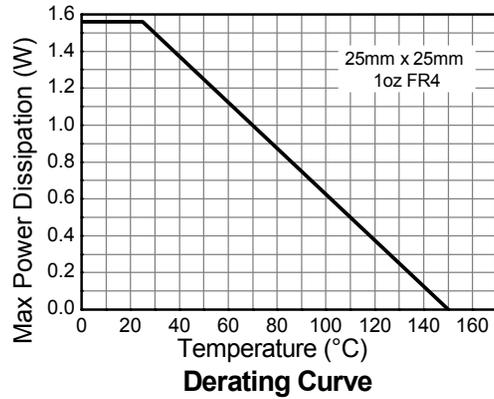
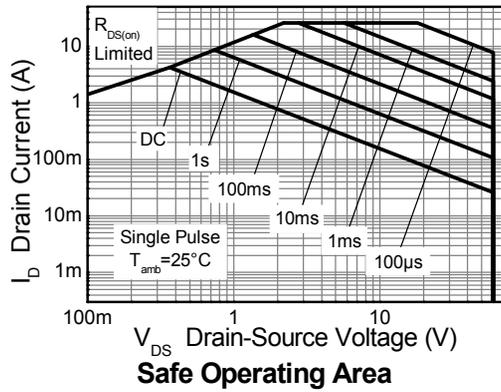
Thermal resistance

Parameter	Symbol	Value	Unit
Junction to ambient (a)	$R_{\theta JA}$	80	$^\circ C/W$
Junction to ambient (b)	$R_{\theta JA}$	45	$^\circ C/W$
Junction to lead (d)	$R_{\theta JL}$	30.2	$^\circ C/W$

NOTES:

- (a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on FR4 PCB measured at $t \leq 10$ sec.
- (c) Repetitive rating on 25mm x 25mm FR4 PCB, $D=0.02$, pulse width 300us – pulse width limited by maximum junction temperature.
- (d) Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal characteristics



Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-Source breakdown voltage	$V_{(BR)DSS}$	60			V	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$
Zero gate voltage drain current	I_{DSS}			1.0	μA	$V_{DS}=60\text{V}, V_{GS}=0\text{V}$
Gate-Body leakage	I_{GSS}			100	nA	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$
Gate-Source threshold voltage	$V_{GS(th)}$	1		3	V	$I_D=250\mu\text{A}, V_{DS}=V_{GS}$
Static Drain-Source on-state resistance (*)	$R_{DS(on)}$			0.050 0.070	Ω	$V_{GS}=10\text{V}, I_D=3.6\text{A}$ $V_{GS}=4.5\text{V}, I_D=3.0\text{A}$
Forward Transconductance (*) (†)	g_{fs}		10.2		S	$V_{DS}=15\text{V}, I_D=4.5\text{A}$
Dynamic (†)						
Input capacitance	C_{iss}		1063		pF	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$ $f=1\text{MHz}$
Output capacitance	C_{oss}		104		pF	
Reverse transfer capacitance	C_{rss}		64		pF	
Switching (‡) (†)						
Turn-on-delay time	$t_{d(on)}$		3.8		ns	$V_{DD}=30\text{V}, V_{GS}=10\text{V}$ $I_D=1\text{A}$ $R_G \cong 6.0\Omega,$
Rise time	t_r		4.0		ns	
Turn-off delay time	$t_{d(off)}$		26.2		ns	
Fall time	t_f		10.6		ns	
Gate charge	Q_g		11.0		nC	$V_{DS}=30\text{V}, V_{GS}=5\text{V}$ $I_D=4.5\text{A}$
Total gate charge	Q_g		20.4		nC	$V_{DS}=30\text{V}, V_{GS}=10\text{V}$ $I_D=4.5\text{A}$
Gate-Source charge	Q_{gs}		4.1		nC	
Gate-Drain charge	Q_{gd}		5.1		nC	
Source-Drain diode						
Diode forward voltage (*)	V_{SD}		0.85	0.95	V	$I_S=5.5\text{A}, V_{GS}=0\text{V}$
Reverse recovery time (‡)	t_{rr}		22.0		ns	$I_S=2.2\text{A}, di/dt=100\text{A}/\mu\text{s}$
Reverse recovery charge (‡)	Q_{rr}		21.4		nC	

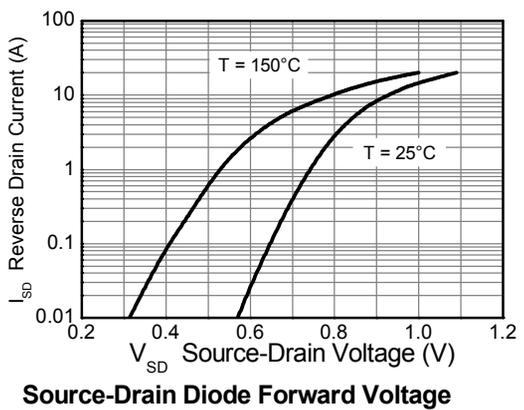
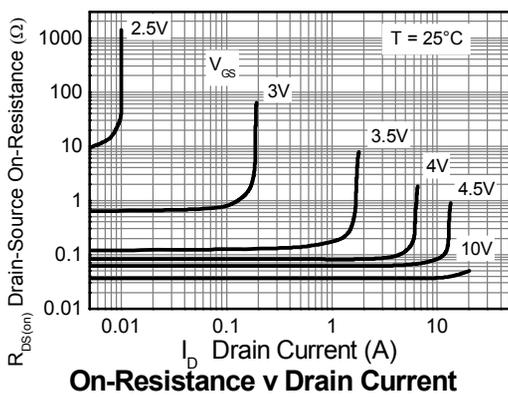
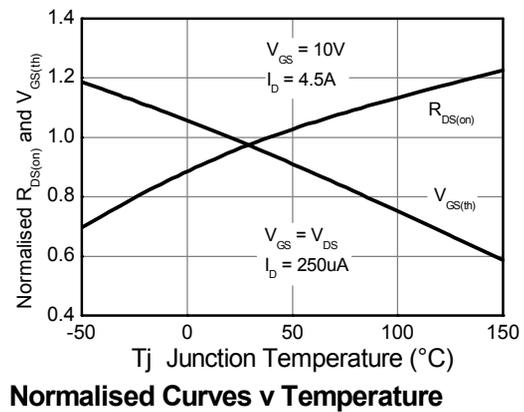
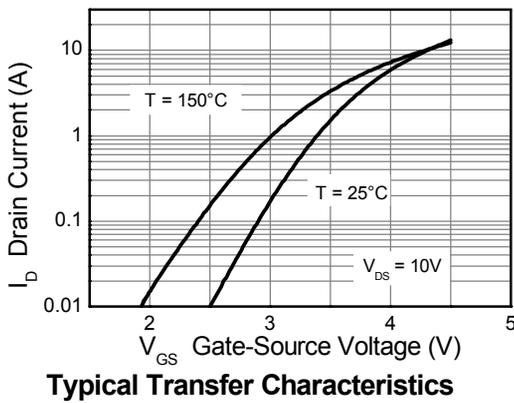
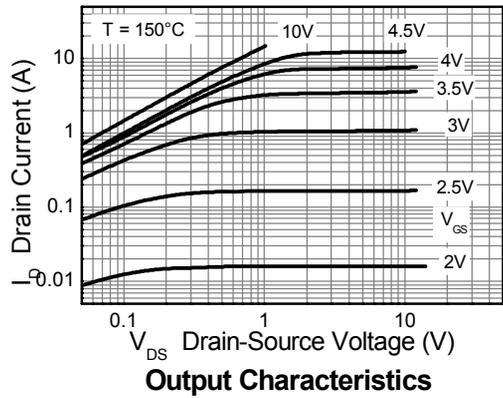
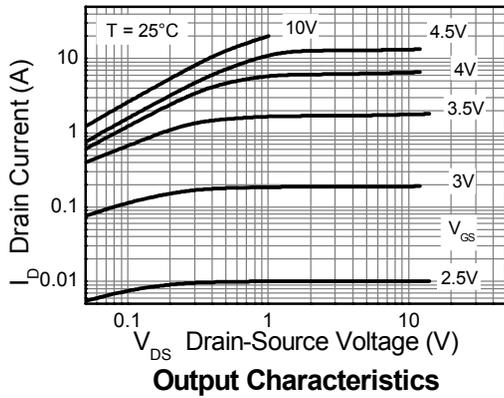
NOTES:

 (*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

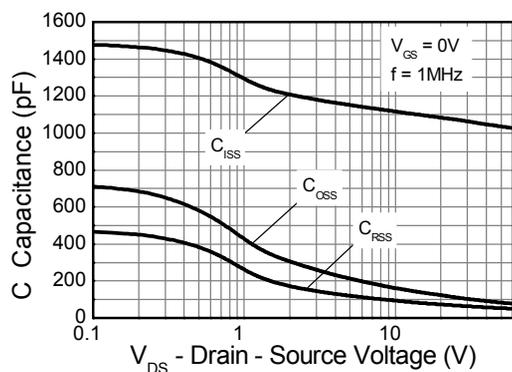
(†) Switching characteristics are independent of operating junction temperature.

(‡) For design aid only, not subject to production testing

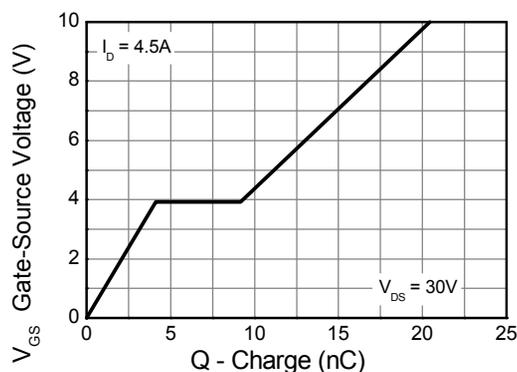
Typical characteristics



Typical characteristics

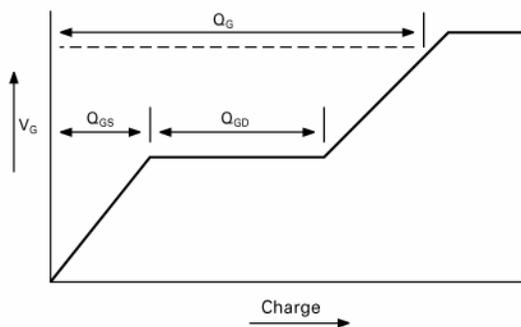


Capacitance v Drain-Source Voltage

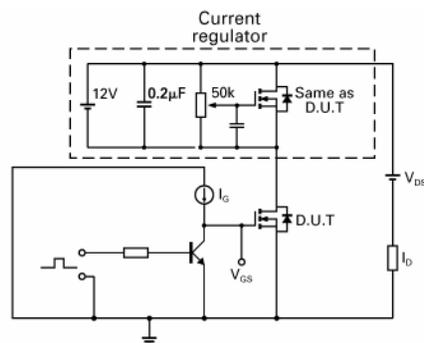


Gate-Source Voltage v Gate Charge

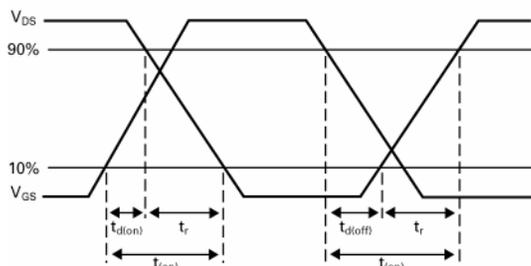
Test circuits



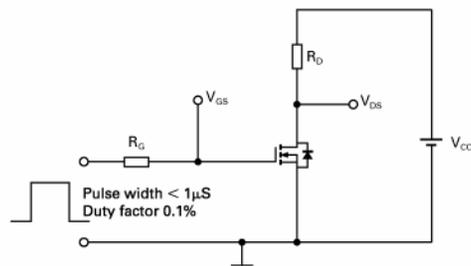
Basic gate charge waveform



Gate charge test circuit

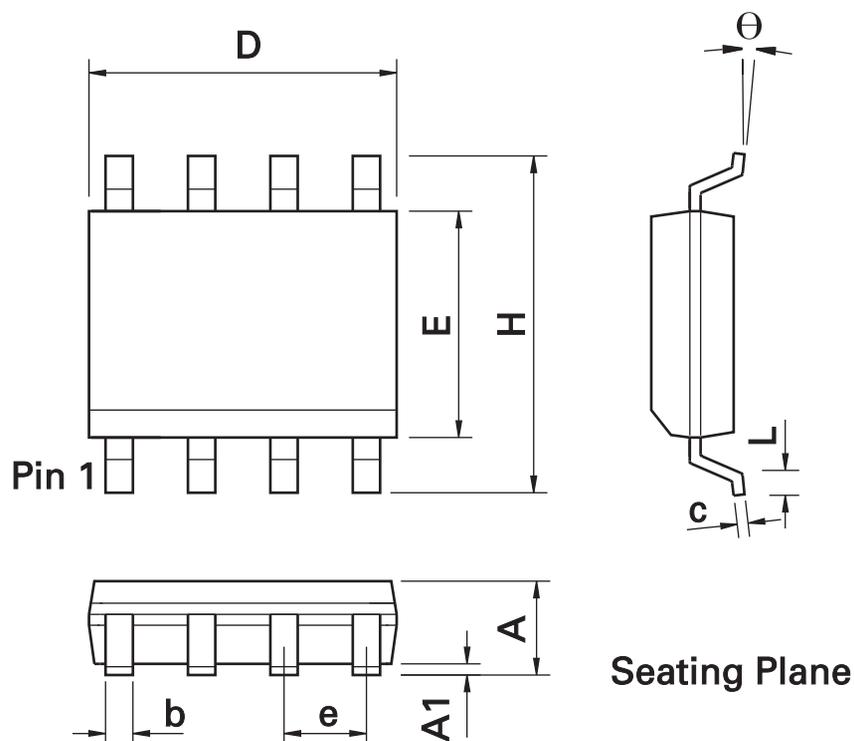


Switching time waveforms



Switching time test circuit

Package outline SO8



SO8 Package Information

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.053	0.069	1.35	1.75	e	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	c	0.008	0.010	0.19	0.25
H	0.228	0.244	5.80	6.20	U	0°	8°	0°	8°
E	0.150	0.157	3.80	4.00	h	0.010	0.020	0.25	0.50
L	0.016	0.050	0.40	1.27	-	-	-	-	-

Note: Controlling dimensions are in inches. Approximate dimensions are provided in millimeters